

## Silicon PNP Power Transistors

## 2N6029 2N6030

## DESCRIPTION

- With TO-3 package
- Complement to type 2N5629 2N5630
- High power dissipations

## APPLICATIONS

- For high voltage and high power amplifier applications

## PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

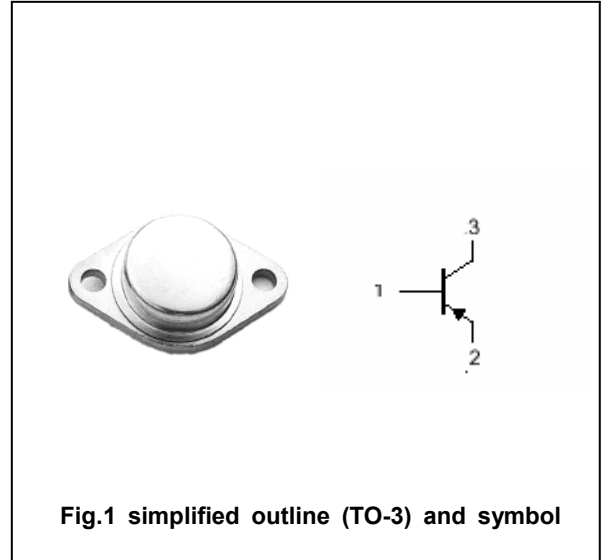


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings( $T_a = \square$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	2N6029	-100	V
		2N6030	-120	
$V_{CEO}$	Collector-emitter voltage	2N6029	-100	V
		2N6030	-120	
$V_{EBO}$	Emitter-base voltage	Open collector	-7	V
$I_C$	Collector current		-16	A
$I_{CM}$	Collector current-peak		-20	A
$I_B$	Base current		-5.0	A
$P_D$	Total Power Dissipation	$T_C = 25 \square$	200	W
$T_j$	Junction temperature		200	$\square$
$T_{stg}$	Storage temperature		-65~200	$\square$

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-c}$	Thermal resistance junction to case	0.875	$\square/W$

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	2N6029	I <sub>C</sub> =-0.2A ; I <sub>B</sub> =0	-100			V
		2N6030		-120			
V <sub>CEsat-1</sub>	Collector-emitter saturation voltage		I <sub>C</sub> =-10A; I <sub>B</sub> =-1A			-1.0	V
V <sub>CEsat-2</sub>	Collector-emitter saturation voltage		I <sub>C</sub> =-16A ; I <sub>B</sub> =-4A			-2.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage		I <sub>C</sub> =-10A; I <sub>B</sub> =-1A			-1.8	V
V <sub>BE</sub>	Base-emitter on voltage		I <sub>C</sub> =-8A ; V <sub>CE</sub> =-2V			-1.5	V
I <sub>CBO</sub>	Collector cut-off current		V <sub>CB</sub> =ratedV <sub>CB0</sub> ; I <sub>E</sub> =0			-1.0	mA
I <sub>CEO</sub>	Collector cut-off current	2N6029	V <sub>CE</sub> =-50V; I <sub>B</sub> =0			-1.0	mA
		2N6030		V <sub>CE</sub> =-60V; I <sub>B</sub> =0			
I <sub>CEV</sub>	Collector cut-off current (V <sub>BE(off)</sub> =1.5V)		V <sub>CE</sub> =ratedV <sub>CB</sub>			-1.0	mA
			V <sub>CE</sub> =ratedV <sub>CB</sub> ; T <sub>C</sub> =150°C			-5.0	
I <sub>EBO</sub>	Emitter cut-off current		V <sub>EB</sub> =-7V; I <sub>C</sub> =0			-1.0	mA
h <sub>FE-1</sub>	DC current gain	2N6029	I <sub>C</sub> =-8A ; V <sub>CE</sub> =-2V	25		100	
		2N6030		20		80	
h <sub>FE-2</sub>	DC current gain		I <sub>C</sub> =-16A ; V <sub>CE</sub> =-2V	4			
C <sub>OB</sub>	Output capacitance		I <sub>E</sub> =0 ; V <sub>CB</sub> =-10V ; f=0.1MHz			1000	pF
f <sub>T</sub>	Transition frequency		I <sub>C</sub> =-1A ; V <sub>CE</sub> =-20V; f=0.5MHz	1.0			MHz

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PACKAGE OUTLINE

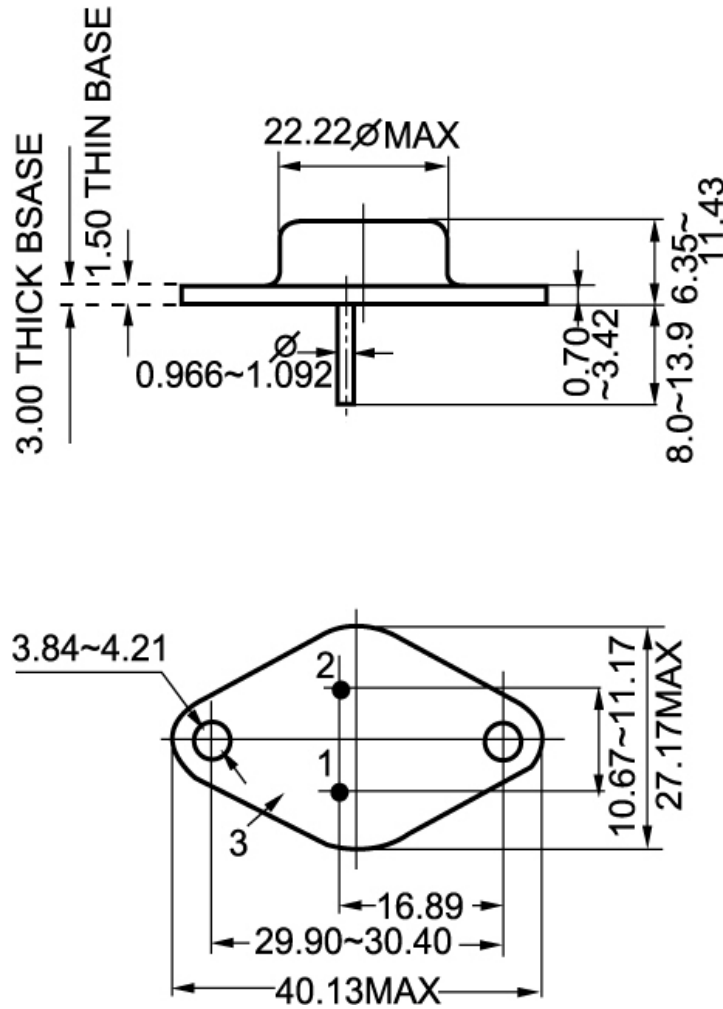


Fig.2 outline dimensions (unindicated tolerance:±0.10mm)